

SC12851ZP

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		Application Number	10/670928		
		Filing Date			
		First Named Inventor	Chun-Li Liu		
		Group Art Unit	2818		
Examiner Name	D. LE				
Sheet		of		Attorney Docket Number	SC12851ZP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
De	AA	5,461,243	10/24/1995	Ek <i>et al.</i>	
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De	AG	2003/0040160 A1	02/27/2003	Huang <i>et al.</i>	

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Examine Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³	Number ⁴ Kind Code ² (if known)			
De	AH	JP	2000243946	12/06/1999	Naoharu <i>et al.</i>	
	AI	WO	02/33746 A1	04/22/2002	Chu <i>et al.</i>	Yes/Abstract

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
De	AJ	Chi <i>et al.</i> , "Electrically active defects in surface preamorphized and subsequently RTP-annealed Si and the effect of titanium silicidation," <i>Proc. 1998 5th International Conference on Solid-State and Integrated Circuit Technology</i> , October 21, 1998, Beijing, China, p. 324-327.	✓	
	AK	Fahey <i>et al.</i> , "Point defects and dopant diffusion in silicon," <i>Reviews of Modern Physics</i> , April 1989, Vol. 61, No. 2, pp. 289-384.	/	
	AL	Lee <i>et al.</i> , "Sub-30 nm P+ abrupt junction formation in Strained Si/Si _{1-x} Ge _x MOS device," <i>Technical Digest of the International Electron Devices Meeting</i> , December 8, 2002, pp. 379-81.	/	
	AM	LeGoues <i>et al.</i> , "Kinetics and Mechanism of Oxidation of SiGe: Dry Versus Wet Oxidation," <i>Applied Physics Letters</i> , February 13, 1989, Vol. 54, No. 7, pp. 644-646.	/	
	AN	LeGoues <i>et al.</i> , "Oxidation Studies of SiGe," <i>Journal of Applied Physics</i> , February 15, 1989, Vol. 65, No. 4, pp. 1724-1728.	/	
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	AP	Sawano <i>et al.</i> , "Relaxation Enhancement of SiGe Thin Layers by Ion Implantation into Si Substrates," <i>IEEE</i> , 2002, pp. 403-404.	/	
	AQ	Tezuka <i>et al.</i> , "Dislocation-free Formation of Relaxed SiGe-on-insulator Layers," <i>Applied Physics Letters</i> , May 13, 2002, Vol. 80, No. 19, pp. 3560-3562.	/	
	AR	Tezuka <i>et al.</i> , "Fabrication of Strained Si on an Ultrathin SiGe-on-insulator Virtual Substrate with a High-Ge Fraction," <i>Applied Physics Letters</i> , September 17, 2001, Vol. 79, No. 12, pp. 1798-1800.	/	
De	AS	Vyatkin <i>et al.</i> , "Ion Beam Induced Strain Relaxation in Pseudomorphous Epitaxial SiGe Layers," <i>IEEE</i> , 2000, pp. 70-72.	/	

Examiner Signature	De	Date Considered	Feb-2005
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¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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